

Product Summary

| BV_{DSS} | $R_{DS(ON)}$ Max | I_D Max $T_A = +25^\circ C$ |
|------------|---------------------------------|----------------------------------|
| 20V | 90m Ω @ $V_{GS} = 4.5V$ | 2.8A |
| | 120m Ω @ $V_{GS} = 2.5V$ | 2.4A |

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control

Mechanical Data

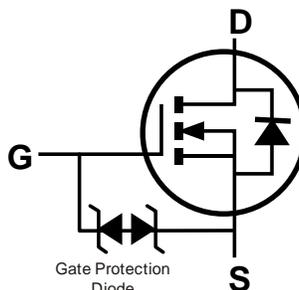
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)



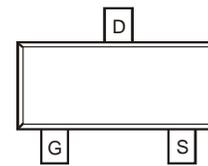
ESD Protected Gate



Top View



Gate Protection Diode
Internal Schematic



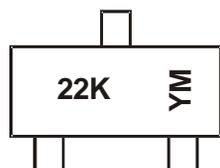
Top View

Ordering Information (Note 5)

| Part Number | Case | Packaging |
|---------------|-------|--------------------|
| DMG2302UKQ-7 | SOT23 | 3,000/Tape & Reel |
| DMG2302UKQ-13 | SOT23 | 10,000/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to <https://www.diodes.com/quality/>.
 5. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



22K = Product Type Marking Code
 YM = Date Code Marking
 Y or Y= Year (ex: F = 2018)
 M = Month (ex: 9 = September)

Date Code Key

| Year | 2015 | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 |
|------|------|------|------|------|------|------|------|------|
| Code | C | D | E | F | G | H | I | J |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|--|--------------|---------------------------|-----------|----------|------|
| Drain-Source Voltage | | | V_{DSS} | 20 | V |
| Gate-Source Voltage | | | V_{GSS} | ± 12 | V |
| Continuous Drain Current (Note 7) $V_{GS} = 4.5\text{V}$ | Steady State | $T_A = +25^\circ\text{C}$ | I_D | 2.8 | A |
| | | $T_A = +70^\circ\text{C}$ | | 2.2 | |
| Maximum Continuous Body Diode Forward Current (Note 7) | | | I_S | 1.1 | A |
| Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%) | | | I_{DM} | 12 | A |

Thermal Characteristics

| Characteristic | | | Symbol | Value | Unit |
|--|--|--------------|-----------------|-------------|--------------------|
| Total Power Dissipation (Note 6) | | | P_D | 0.66 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | | Steady State | $R_{\theta JA}$ | 192 | $^\circ\text{C/W}$ |
| Total Power Dissipation (Note 7) | | | P_D | 1.1 | W |
| Thermal Resistance, Junction to Ambient (Note 7) | | Steady State | $R_{\theta JA}$ | 115 | $^\circ\text{C/W}$ |
| Operating and Storage Temperature Range | | | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ |

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|--|--------------|-----|-----|----------|---------------|---|
| OFF CHARACTERISTICS (Note 8) | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | 20 | — | — | V | $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$ |
| Zero Gate Voltage Drain Current | I_{DSS} | — | — | 10 | μA | $T_J = +25^\circ\text{C}, V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$ |
| Gate-Source Leakage | I_{GSS} | — | — | ± 10 | μA | $V_{GS} = \pm 10\text{V}, V_{DS} = 0\text{V}$ |
| ON CHARACTERISTICS (Note 8) | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | 0.3 | 0.6 | 1.0 | V | $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$ |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | — | 61 | 90 | m Ω | $V_{GS} = 4.5\text{V}, I_D = 3.6\text{A}$ |
| | | | 80 | 120 | | $V_{GS} = 2.5\text{V}, I_D = 3.1\text{A}$ |
| Diode Forward Voltage | V_{SD} | — | 0.7 | 1.2 | V | $V_{GS} = 0\text{V}, I_S = 1.0\text{A}$ |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | |
| Input Capacitance | C_{iss} | — | 130 | — | pF | $V_{DS} = 10\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$ |
| Output Capacitance | C_{oss} | — | 26 | — | pF | |
| Reverse Transfer Capacitance | C_{rss} | — | 18 | — | pF | |
| Gate Resistance | R_g | — | 2.7 | — | Ω | $V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$ |
| Total Gate Charge ($V_{GS} = 4.5\text{V}$) | Q_g | — | 1.4 | — | nC | $V_{DS} = 10\text{V}, I_D = 3.6\text{A}$ |
| Total Gate Charge ($V_{GS} = 10\text{V}$) | Q_g | — | 2.8 | — | nC | |
| Gate-Source Charge | Q_{gs} | — | 0.1 | — | nC | |
| Gate-Drain Charge | Q_{gd} | — | 0.5 | — | nC | |
| Turn-On Delay Time | $t_{D(ON)}$ | — | 0.6 | — | ns | $V_{DS} = 10\text{V}, V_{GS} = 4.5\text{V},$ $R_g = 1\Omega, R_L = 2.78\Omega$ |
| Turn-On Rise Time | t_r | — | 2.7 | — | ns | |
| Turn-Off Delay Time | $t_{D(OFF)}$ | — | 4.2 | — | ns | |
| Turn-Off Fall Time | t_f | — | 1.7 | — | ns | |
| Reverse Recovery Time | t_{RR} | — | 5.3 | — | ns | $I_F = 3.6\text{A}, di/dt = 100\text{A}/\mu\text{s}$ |
| Reverse Recovery Charge | Q_{RR} | — | 0.5 | — | nC | $I_F = 3.6\text{A}, di/dt = 100\text{A}/\mu\text{s}$ |

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout.
 - Device mounted on 1" x 1" FR-4 PCB with high-coverage 2oz copper, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

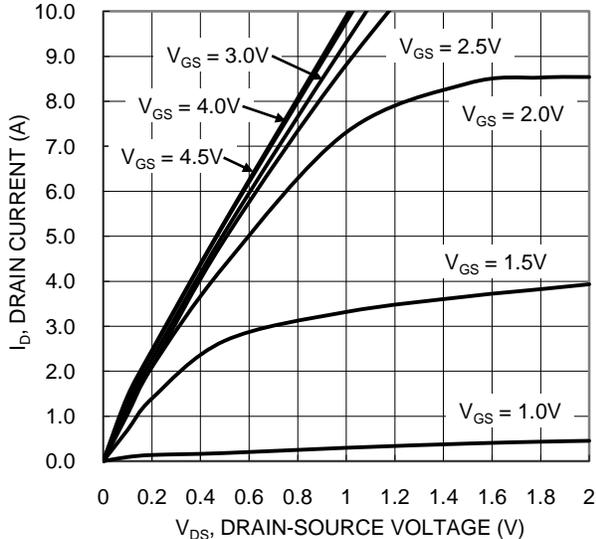


Figure 1. Typical Output Characteristic

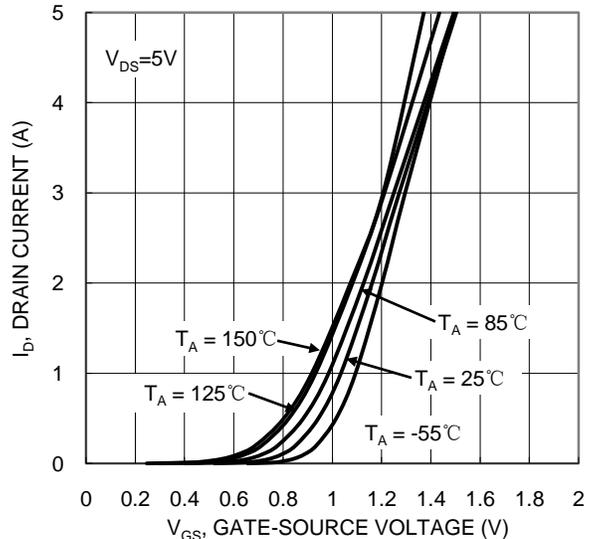


Figure 2. Typical Transfer Characteristic

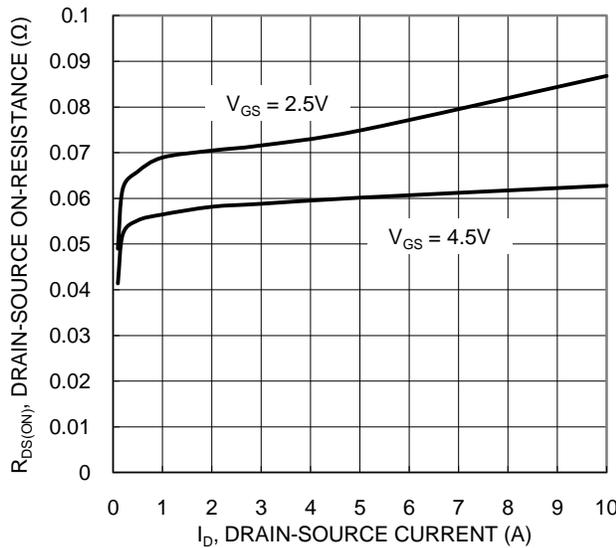


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

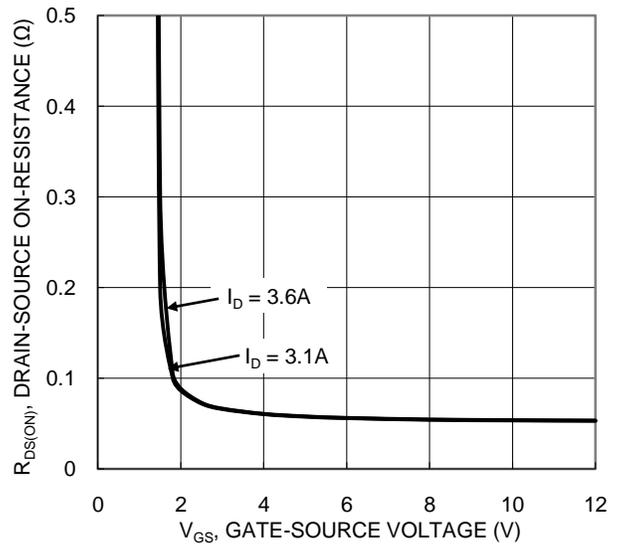


Figure 4. Typical Transfer Characteristic

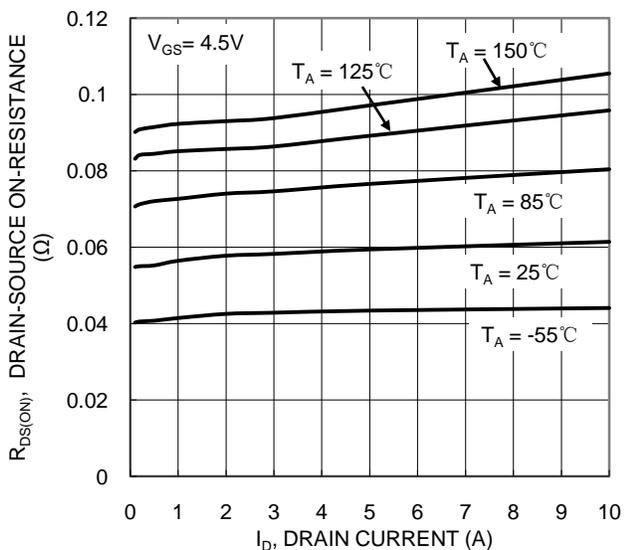


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

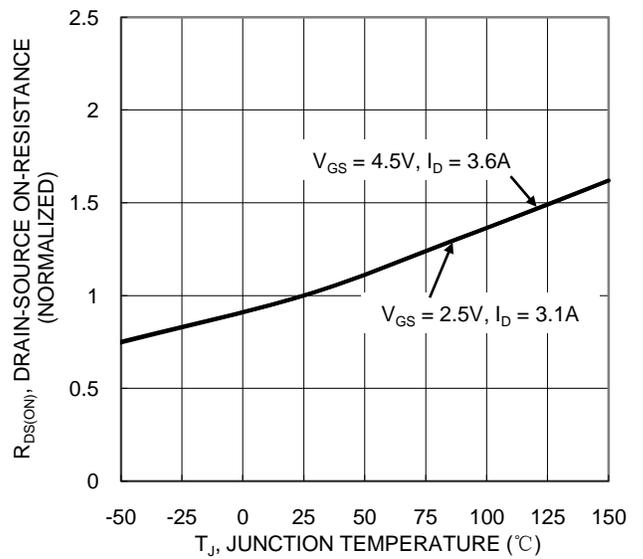


Figure 6. On-Resistance Variation with Junction Temperature

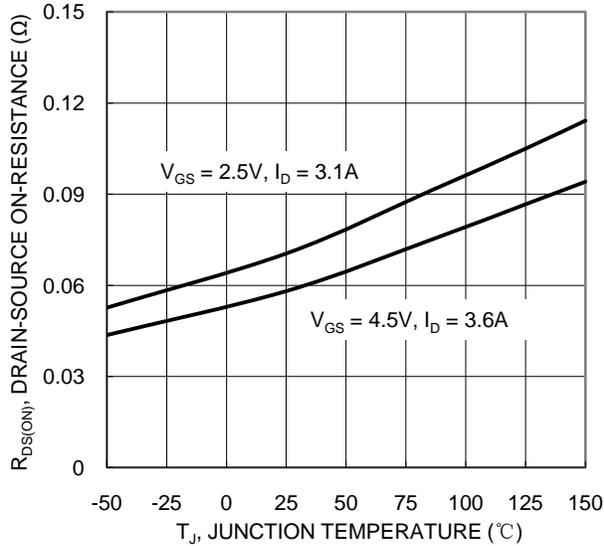


Figure 7. On-Resistance Variation with Junction Temperature

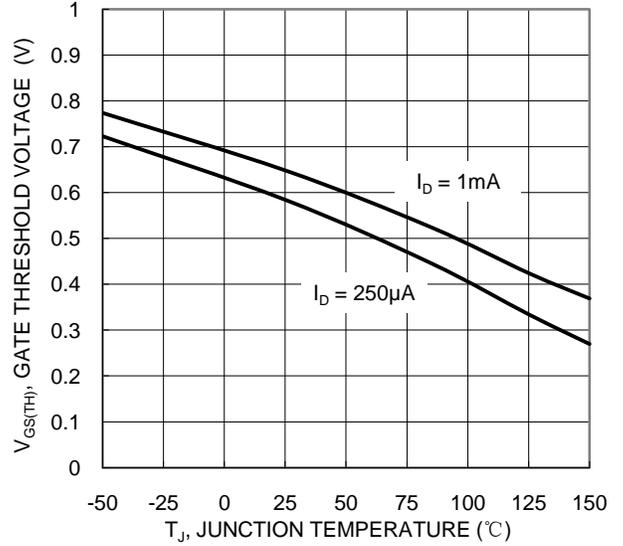


Figure 8. Gate Threshold Variation vs. Junction Temperature

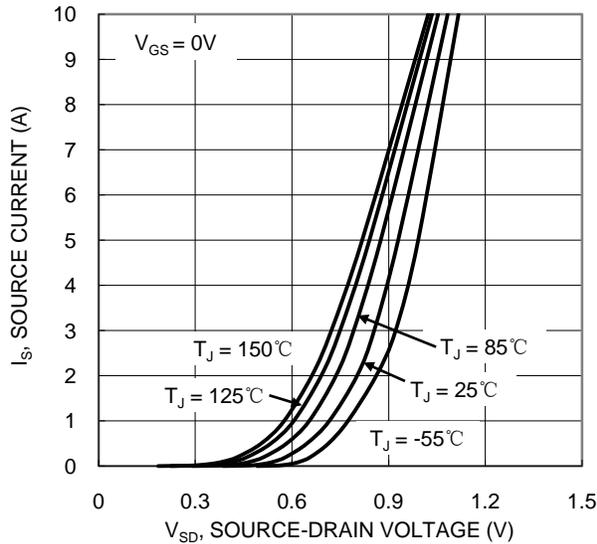


Figure 9. Diode Forward Voltage vs. Current

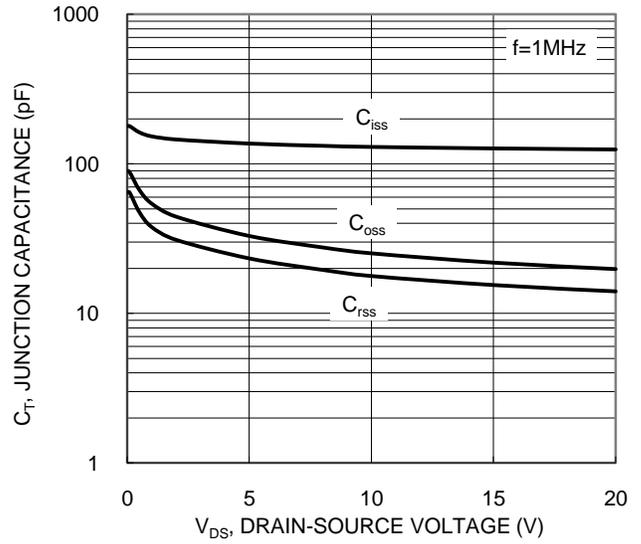


Figure 10. Typical Junction Capacitance

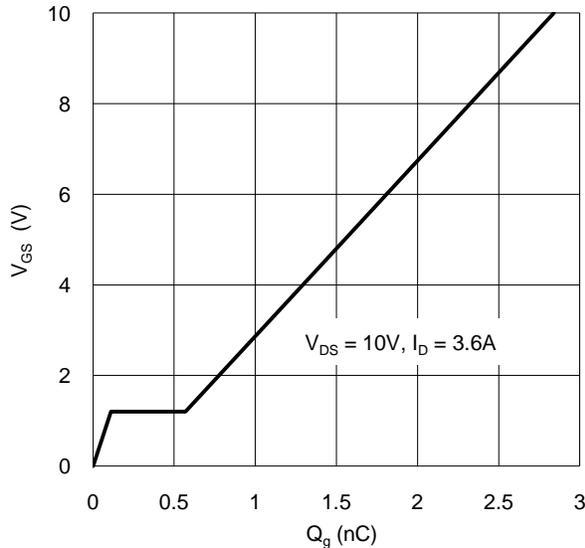


Figure 11. Gate Charge

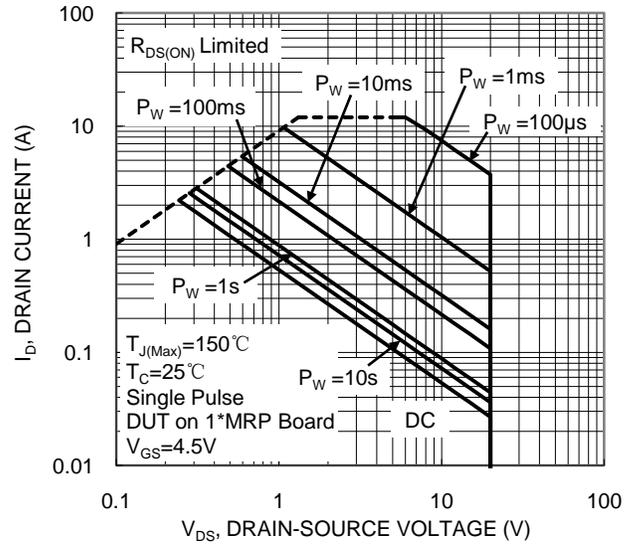


Figure 12. SOA, Safe Operation Area

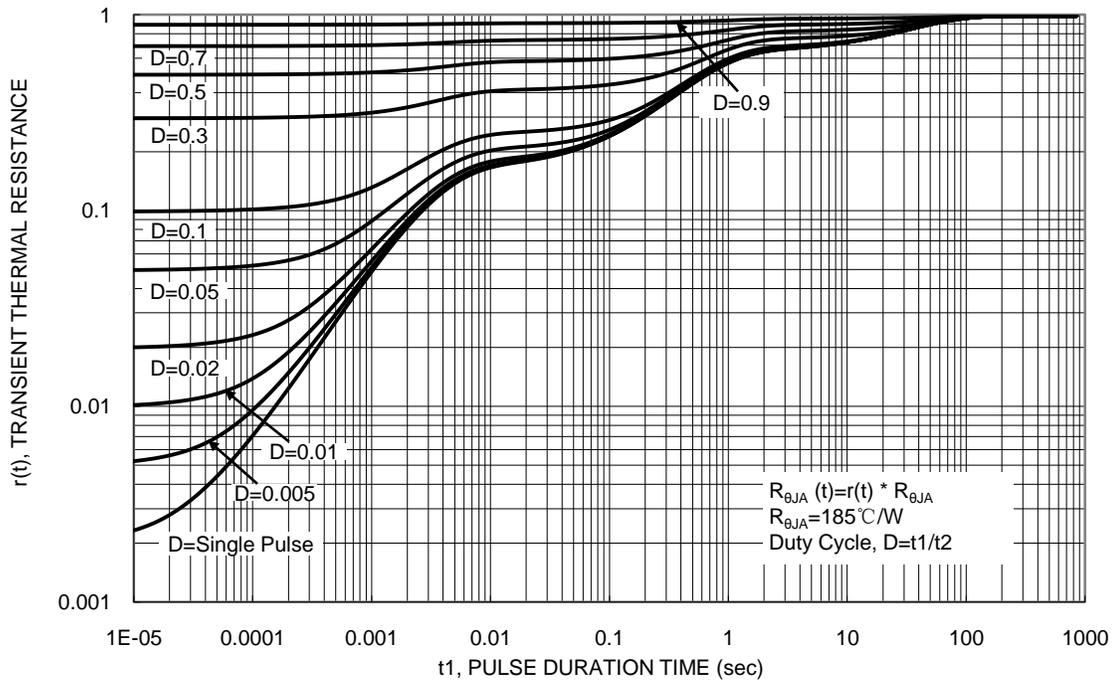
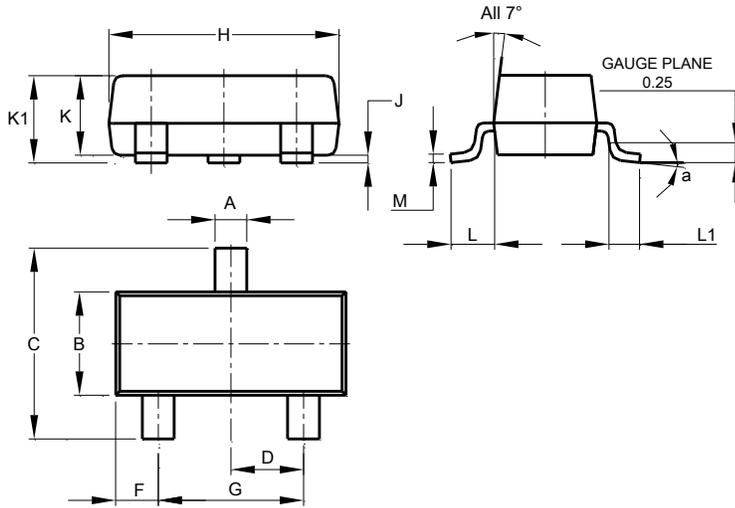


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

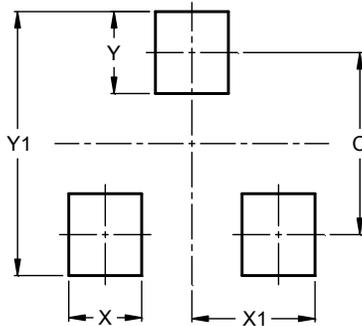


| SOT23 | | | |
|----------------------|-------|-------|-------|
| Dim | Min | Max | Typ |
| A | 0.37 | 0.51 | 0.40 |
| B | 1.20 | 1.40 | 1.30 |
| C | 2.30 | 2.50 | 2.40 |
| D | 0.89 | 1.03 | 0.915 |
| F | 0.45 | 0.60 | 0.535 |
| G | 1.78 | 2.05 | 1.83 |
| H | 2.80 | 3.00 | 2.90 |
| J | 0.013 | 0.10 | 0.05 |
| K | 0.890 | 1.00 | 0.975 |
| K1 | 0.903 | 1.10 | 1.025 |
| L | 0.45 | 0.61 | 0.55 |
| L1 | 0.25 | 0.55 | 0.40 |
| M | 0.085 | 0.150 | 0.110 |
| a | 0° | 8° | -- |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 2.0 |
| X | 0.8 |
| X1 | 1.35 |
| Y | 0.9 |
| Y1 | 2.9 |

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